

## DN6003 N-Channel MOSFET

### **General description**

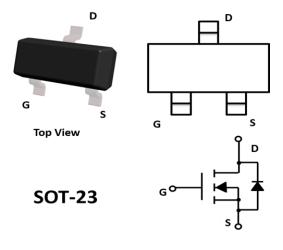
N-Channel MOSFET

#### **FEATURES**

- V<sub>DS</sub>=60V
- I<sub>D</sub>=3A
- $R_{DS(ON)}$ ( at  $V_{GS}$ =10V)<100  $m\Omega$
- R<sub>DS(ON)</sub>( at V<sub>GS</sub>=4.5V)<110 m $\Omega$
- Trench Power MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low R<sub>DS(ON)</sub>

#### **APPLICATIONS**

- DC-DC Converters
- · Power management functions



#### **Device Marking Code:**

Device Type	Device Marking
DN6003	6003

### **Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-source Voltage		$V_{ extsf{DS}}$	60	V	
Gate-source Voltage		$V_{GS}$	±20	>	
D : 0 .	T <sub>A</sub> =25℃		3	А	
Drain Current	T <sub>A</sub> =70℃	I <sub>D</sub>	2.4		
Pulsed Drain Current <sup>A</sup>		l <sub>DM</sub>	12	Α	
Total Power Dissipation @ T <sub>C</sub> =	<b>-25</b> ℃	P <sub>D</sub>	1.2	W	
Thermal Resistance Junction-	to-Ambient <sup>B</sup>	R <sub>θ</sub> JA	105	°C/ W	
Junction and Storage Temperature Range		Тл ,Твтв	-55~+150	$^{\circ}$ C	

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# **DN6003**



## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	60			V
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V			1	μА
	lgss1	$V_{GS}$ = $\pm 20$ V, $V_{DS}$ =0V			±100	nA
Gate-Body Leakage Current	lgss2	$V_{GS}$ = $\pm 10V$ , $V_{DS}$ = $0V$			±50	nA
Gate Threshold Voltage	VGS(th)	$V_{DS}$ = $V_{GS}$ , $I_D$ =250 $\mu$ A	1.0	1.7	2.0	V
		V <sub>GS</sub> = 10V, I <sub>D</sub> =3A		58	100	
Static Drain-Source On-Resistance	Rds(ON)	V <sub>GS</sub> = 4.5V, I <sub>D</sub> =1.5A		70	110	mΩ
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =3.0A,V <sub>GS</sub> =0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	Is				3.0	Α
Dynamic Parameters				1		
Input Capacitance	C <sub>iss</sub>			330		
Output Capacitance	$C_{oss}$	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,f=1MHZ		90		pF
Reverse Transfer Capacitance	$C_{rss}$			17		
Switching Parameters						
Total Gate Charge	$Q_g$			5.1		
Gate-Source Charge	$Q_{gs}$	V <sub>GS</sub> =10V,V <sub>DS</sub> =30V,I <sub>D</sub> =3.0A		1.3		nC
Gate-Drain Charge	$Q_{\rm gd}$			1.7		
Turn-on Delay Time	t <sub>D(on)</sub>			13		
Turn-on Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DD}$ =30V,		51		
Turn-off Delay Time	t <sub>D(off)</sub>	$I_{D}$ =1.5A,R <sub>L</sub> =1 $\Omega$ R <sub>GEN</sub> =3 $\Omega$		19		ns
Turn-off fall Time	t <sub>f</sub>			12		1

A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

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B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



## **Typical Characteristics**

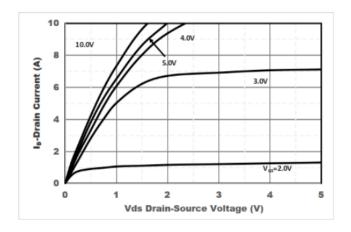


Figure 1. Output Characteristics

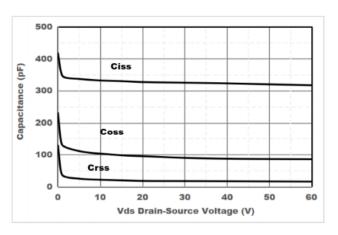


Figure 3. Capacitance Characteristics

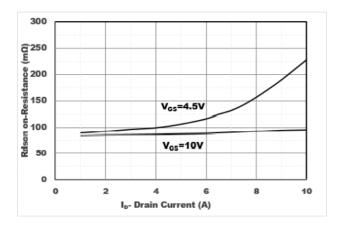


Figure 5. Drain-Source on Resistance

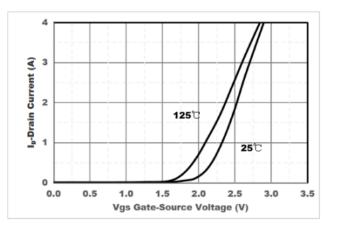


Figure 2. Transfer Characteristics

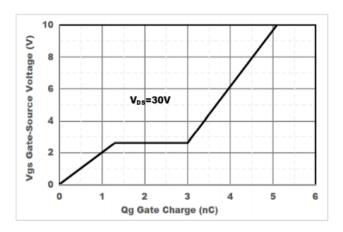


Figure 4. Gate Charge

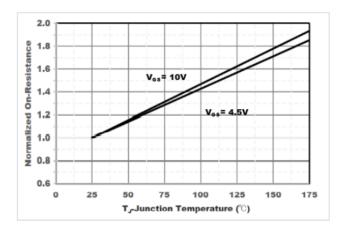
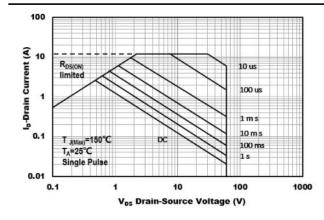


Figure6. Drain-Source on Resistance

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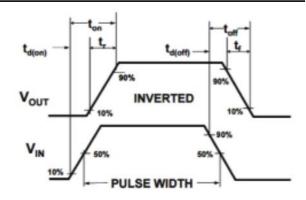
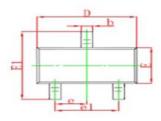
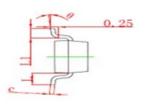


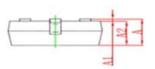
Figure 7. Safe Operation Area

Figure8. Switching wave

## **SOT-23 Package information**

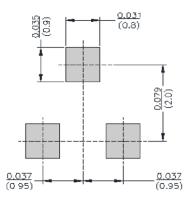






Cumbal	Dimentions in Millimeter		Dimentions in Inches	
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 °

#### **SOT-23 Suggested Pad Layout**



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